

### N-Channel Enhancement Mode MOSFET

#### **Description**

The IRLML2030PbF uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 30V I_D = 4A$ 

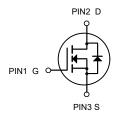
 $R_{DS(ON)}$  < 38m $\Omega$  @  $V_{GS}$ =10V

# **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

#### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
IRLML2030PbF	SOT-23	HXY MOSFET	3000

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	4	А
Ірм	Drain Current-Pulsed (Note 1)	16.4	А
P <sub>D</sub>	Maximum Power Dissipation	1	W
Тл,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	1	±100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.5	2.5	V
D	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	-	29	38	mΩ
$R_{DS(on)}$		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	45	65	11122
$C_{iss}$	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	_	233	-	рF
Coss	Output Capacitance		-	44	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	33	-	pF
Qg	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =2A,	-	3	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	0.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge	V <sub>GS</sub> =10V	-	0.8	-	nC
$t_{d(on)}$	Turn-on Delay Time	V <sub>DS</sub> =15V, I <sub>D</sub> =4A, R <sub>GEN</sub> =3Ω,	_	4	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	2.1	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	15	-	ns
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> =10V	-	3.2	-	ns
Is	Maximum Continuous Drain to Source	Diode Forward	_	_	4	Α
15	Current		-	-	4	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	Α
$V_{\text{SD}}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



### **Typical Characteristics**

Figure1: Output Characteristics

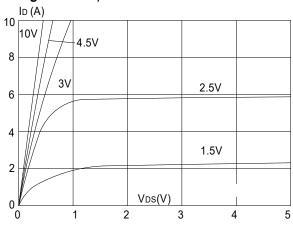


Figure 2: Typical Transfer Characteristics

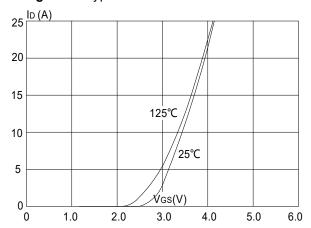


Figure 3:On-resistance vs. Drain Current

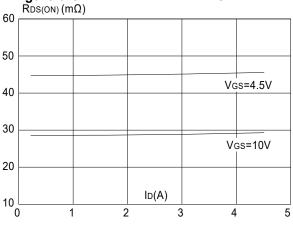


Figure 4: Body Diode Characteristics

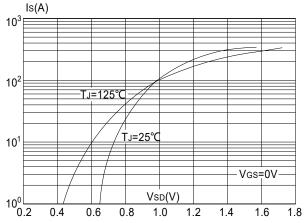


Figure 5: Gate Charge Characteristics

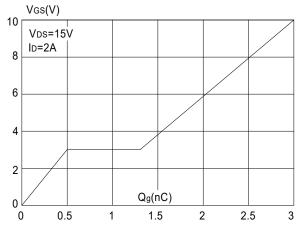
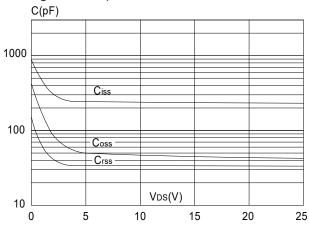
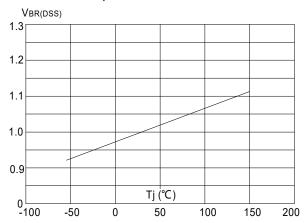


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



**Figure 8:** Normalized on Resistance vs. Junction Temperature

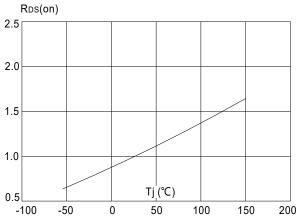
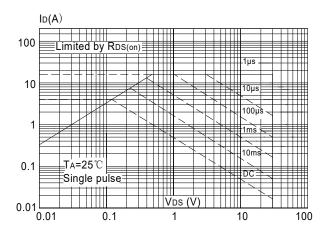
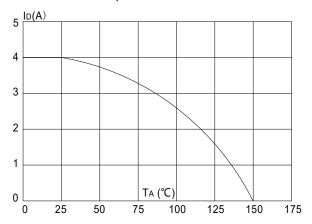


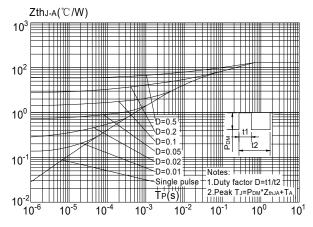
Figure 9: Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

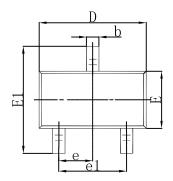


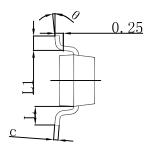
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

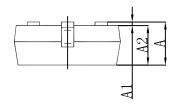




# **SOT-23 Package Outline Dimensions**

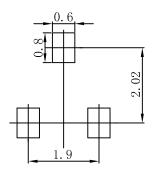






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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